

ABSTRACT OF THE DISCLOSURE

The object of the present invention is to provide a semiconductor device including a circuit employing two or more field-effect transistors that are desired to have equal characteristics, capable of realizing high reliability and superior transistor characteristics. The transistors which are desired to have equal characteristics are placed in the semiconductor device so as to have the same STI trench width (the width of shallow trench isolation adjacent to an active region in which the transistor is formed). By such composition, stress growing in the active region due to the shallow trench isolation is equalized among the transistors and thereby the characteristics of the transistors can be equalized.